



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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### MG12100D-BA1MM




#### Features

- Ultra low loss
- High ruggedness
- High short circuit capability
- Positive temperature coefficient
- With fast free-wheeling diodes

#### Applications

- Inverter
- Converter
- Welder
- SMPS and UPS
- Induction heating

#### Agency Approvals

AGENCY	AGENCY FILE NUMBER
	E71639

#### Module Characteristics ( $T_c = 25^\circ\text{C}$ , unless otherwise specified)

Symbol	Parameters	Test Conditions	Min	Typ	Max	Unit
$R_{thJC}$	Junction-to-Case Thermal Resistance	Per IGBT			0.15	K/W
$R_{thJD}$		Per Inverse Diode			0.30	K/W
Torque	Module-to-Sink	Recommended (M6)	3		5	N·m
Torque	Module Electrodes	Recommended (M5)	2.5		5	N·m
Weight				285		g

#### Absolute Maximum Ratings ( $T_c = 25^\circ\text{C}$ , unless otherwise specified)

Symbol	Parameters	Test Conditions	Values	Unit
<b>IGBT</b>				
$V_{CES}$	Collector - Emitter Voltage		1200	V
$V_{GES}$	Gate - Emitter Voltage		$\pm 20$	V
$I_c$	DC Collector Current	$T_c=25^\circ\text{C}$	160	A
		$T_c=80^\circ\text{C}$	100	A
$I_{cpuls}$	Pulsed Collector Current	$T_c=25^\circ\text{C}, t_p=1\text{ms}$	340	A
		$T_c=80^\circ\text{C}, t_p=1\text{ms}$	220	
$P_{tot}$	Power Dissipation Per IGBT		1000	W
$T_J$	Junction Temperature Range		-40 to +150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range		-40 to +125	$^\circ\text{C}$
$V_{isol}$	Insulation Test Voltage	AC, $t=1\text{min}$	3000	V
<b>Diode</b>				
$V_{RRM}$	Repetitive Reverse Voltage		1200	V
$I_{F(AV)}$	Average Forward Current	$T_c=25^\circ\text{C}$	180	A
		$T_c=80^\circ\text{C}$	120	A
$I_{F(RMS)}$	RMS Forward Current		180	A
$I_{FSM}$	Non-Repetitive Surge Forward Current	$T_J=45^\circ\text{C}, t=10\text{ms}, \text{Sine}$	860	A
		$T_J=45^\circ\text{C}, t=8.3\text{ms}, \text{Sine}$	900	

Life Support Note:

#### Not Intended for Use in Life Support or Life Saving Applications

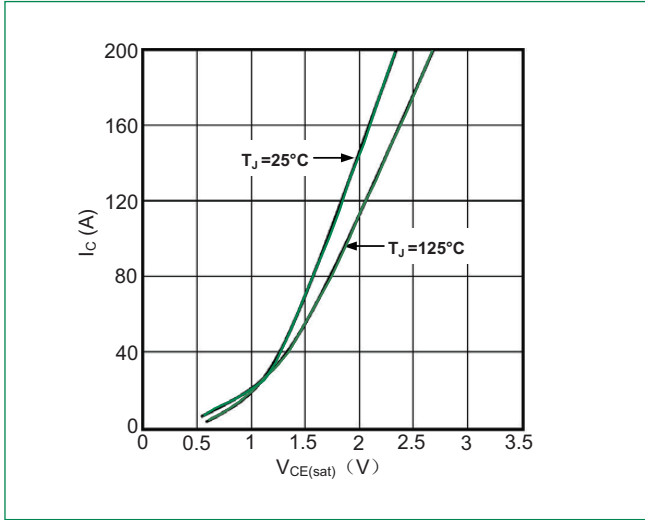
The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

MG12100D-BA1MM

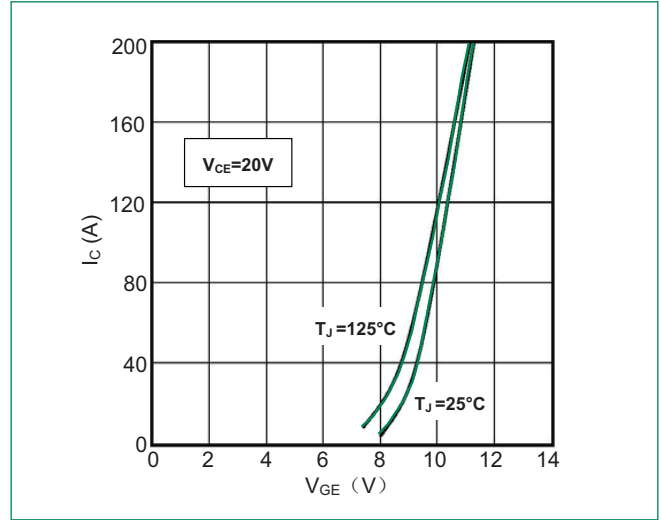
### Electrical and Thermal Specifications ( $T_c = 25^\circ\text{C}$ , unless otherwise specified)

Symbol	Parameters	Test Conditions	Min	Typ	Max	Unit	
<b>IGBT</b>							
$V_{GE(th)}$	Gate - Emitter Threshold Voltage	$V_{CE}=V_{GE}, I_C=4\text{mA}$	5.0	6.2	7.0	V	
$V_{CE(sat)}$	Collector - Emitter Saturation Voltage	$I_C=100\text{A}, V_{GE}=15\text{V}, T_J=25^\circ\text{C}$		1.8		V	
		$I_C=100\text{A}, V_{GE}=15\text{V}, T_J=125^\circ\text{C}$		2.0		V	
$I_{CES}$	Collector Leakage Current	$V_{CE}=1200\text{V}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$			1	mA	
		$V_{CE}=1200\text{V}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$		4		mA	
$I_{GES}$	Gate Leakage Current	$V_{CE}=0\text{V}, V_{GE}=\pm 20\text{V}$	-400		400	nA	
$Q_{ge}$	Gate Charge	$V_{CC}=600\text{V}, I_C=100\text{A}, V_{GE}=\pm 15\text{V}$		1200		nC	
$C_{ies}$	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$		8.58		nF	
$C_{oes}$	Output Capacitance			0.6			
$C_{res}$	Reverse Transfer Capacitance			0.4			
$t_{d(on)}$	Turn - on Delay Time	$V_{CC}=600\text{V}$ $I_C=100\text{A}$ $R_G=9\Omega$ $V_{GE}=\pm 15\text{V}$ Inductive Load	$T_J=25^\circ\text{C}$		270		ns
			$T_J=125^\circ\text{C}$		290		ns
$t_r$	Rise Time		$T_J=25^\circ\text{C}$		60		ns
			$T_J=125^\circ\text{C}$		60		ns
$t_{d(off)}$	Turn - off Delay Time		$T_J=25^\circ\text{C}$		480		ns
			$T_J=125^\circ\text{C}$		550		ns
$t_f$	Fall Time		$T_J=25^\circ\text{C}$		60		ns
			$T_J=125^\circ\text{C}$		65		ns
$E_{on}$	Turn - on Energy		$T_J=25^\circ\text{C}$		12		mJ
			$T_J=125^\circ\text{C}$		16.8		mJ
$E_{off}$	Turn - off Energy	$T_J=25^\circ\text{C}$		7.4		mJ	
		$T_J=125^\circ\text{C}$		11.6		mJ	
<b>Diode</b>							
$V_F$	Forward Voltage	$I_F=100\text{A}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$		1.9	2.3	V	
		$I_F=100\text{A}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$		1.7	2.1	V	
$t_{rr}$	Reverse Recovery Time	$I_F=100\text{A}, V_R=800\text{V}$ $di_F/dt=-1000\text{A}/\mu\text{s}$ $T_J=125^\circ\text{C}$		230		ns	
$I_{RRM}$	Max. Reverse Recovery Current			80		A	
$Q_{rr}$	Reverse Recovery Charge			9.7		$\mu\text{C}$	

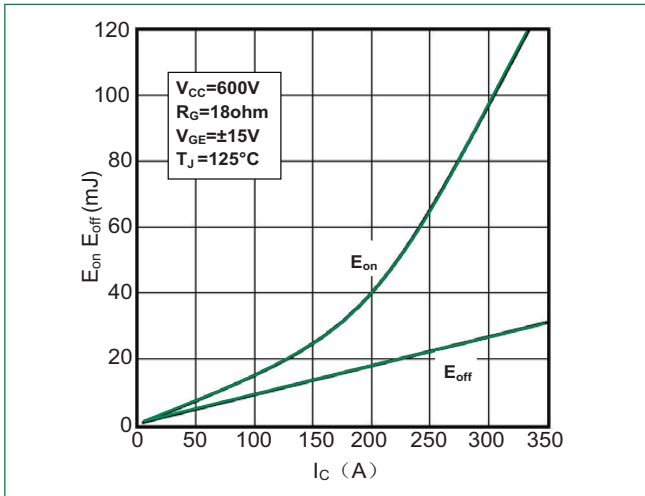
**Figure 1: Typical Output Characteristics**



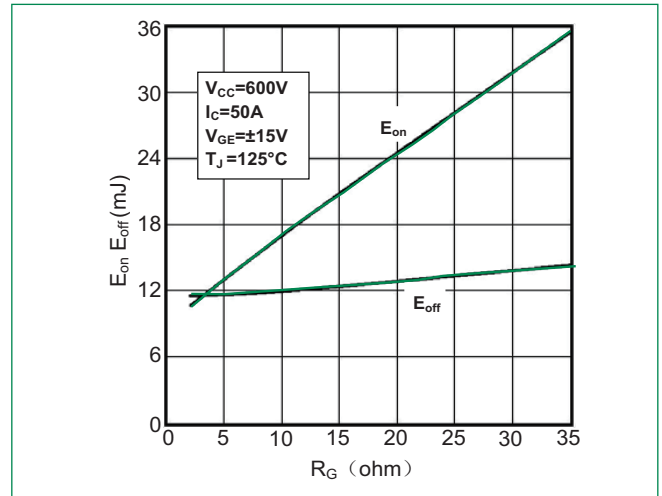
**Figure 2: Typical Transfer characteristics**



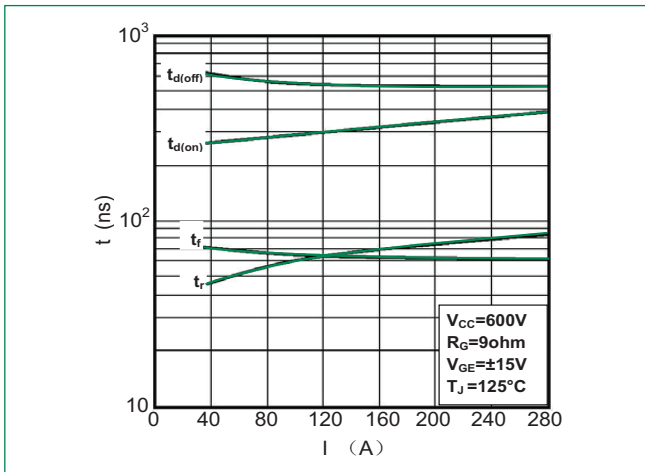
**Figure 3: Switching Energy vs. Collector Current**



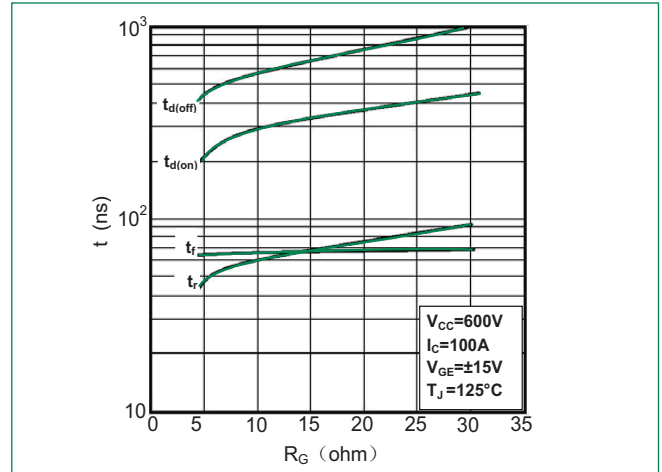
**Figure 4: Switching Energy vs. Gate Resistor**



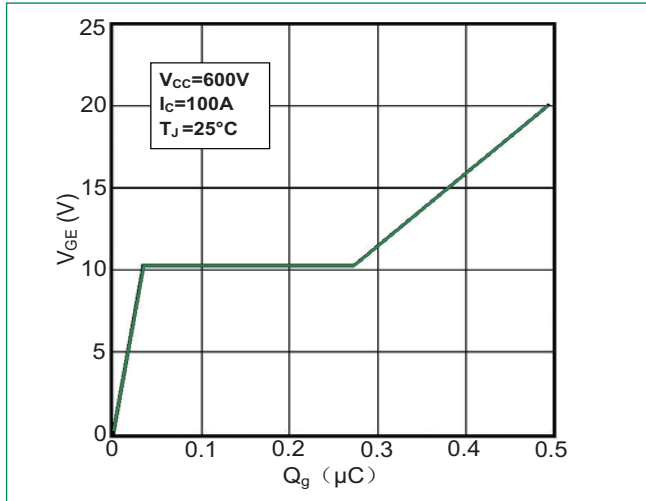
**Figure 5: Switching Times vs. Collector Current**



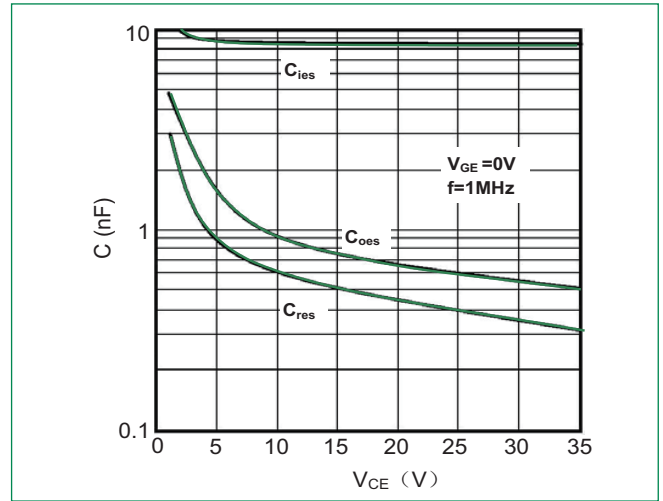
**Figure 6: Switching Times vs. Gate Resistor**



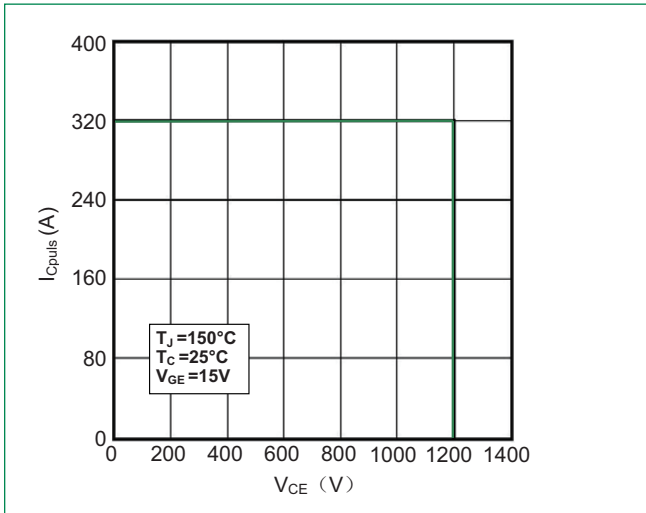
**Figure 7: Gate Charge characteristics**



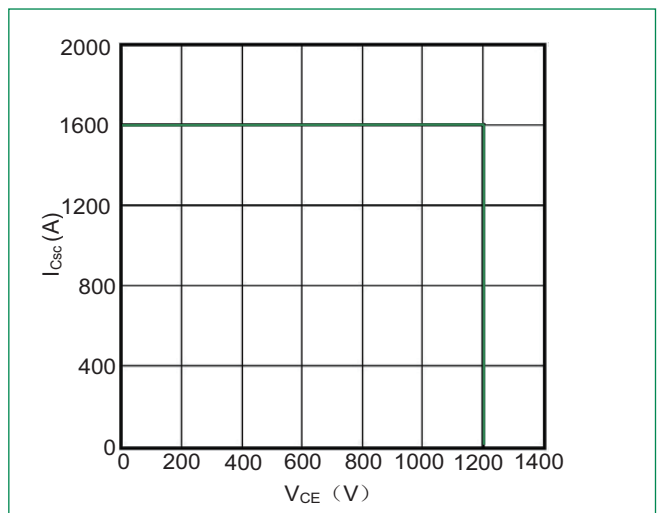
**Figure 8: Typical Capacitances vs.  $V_{CE}$**



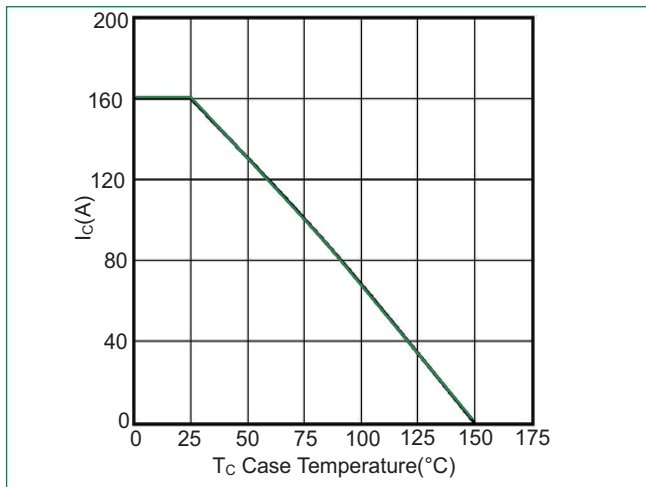
**Figure 9: Reverse Biased Safe Operating Area**



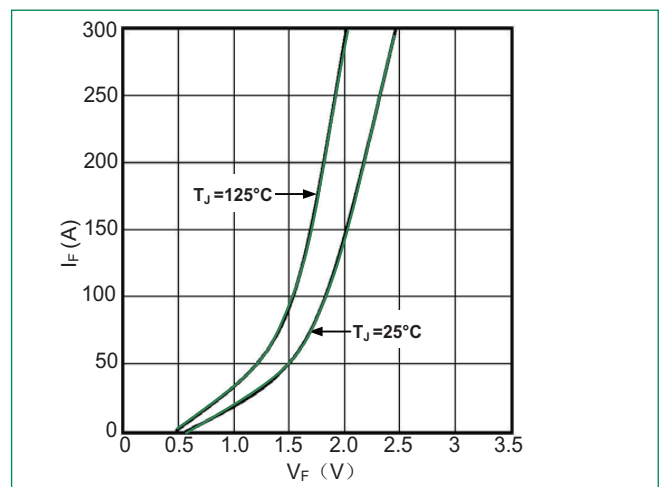
**Figure 10: Short Circuit Safe Operating Area**



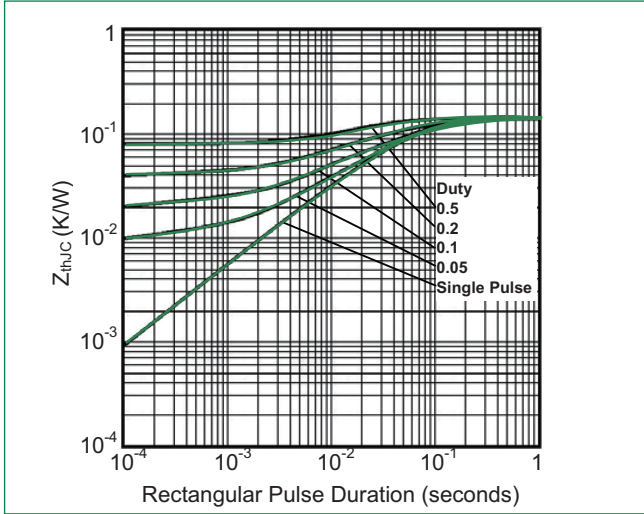
**Figure 11: Rated Current vs.  $T_c$**



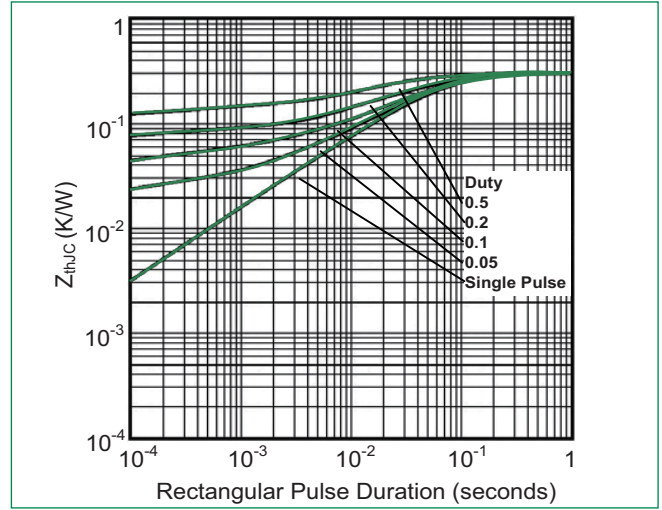
**Figure 12: Diode Forward Characteristics**



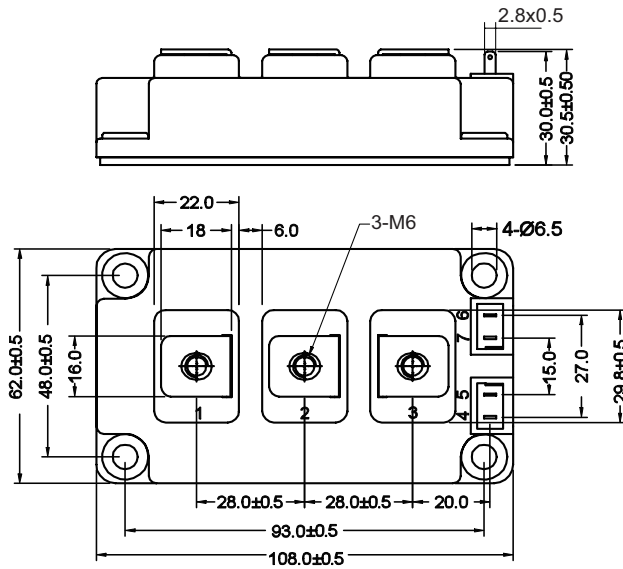
**Figure 13: Transient Thermal Impedance of IGBT**



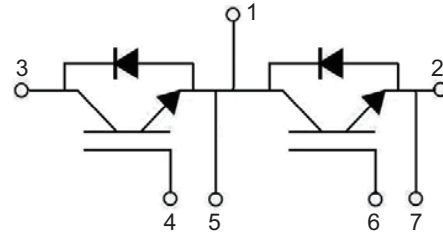
**Figure 14: Transient Thermal Impedance of Diode**



**Dimensions-Package D**



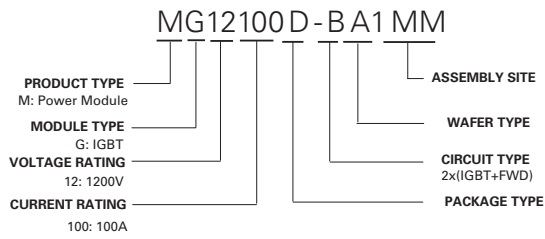
**Circuit Diagram**



### Packing Options

Part Number	Marking	Weight	Packing Mode	M.O.Q
MG12100D-BA1MM	MG12100D-BA1MM	285g	Bulk Pack	60

### Part Numbering System



### Part Marking System

